



# DA2610100L

Silicon epitaxial planar type

For high speed switching circuits  
 DA27101 in ML2 type package

■ Features

- Small reverse current IR
- Short reverse recovery time trr
- Halogen-free / RoHS compliant  
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: B1

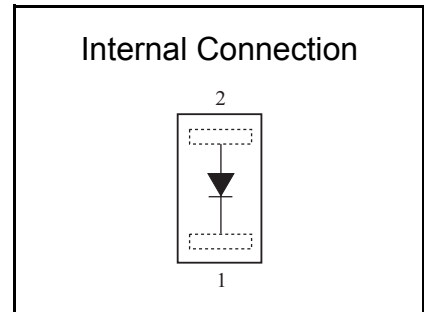
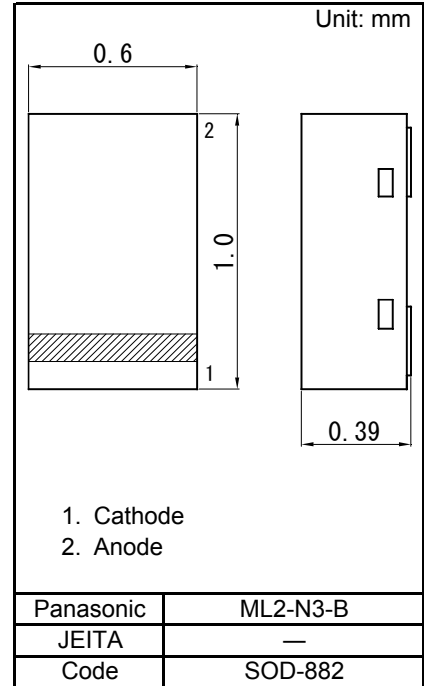
■ Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

| Parameter                                    | Symbol | Rating      | Unit |
|--|--------|-------------|------|
| Reverse voltage                              | VR     | 80          | V    |
| Maximum peak reverse voltage                 | VRM    | 80          | V    |
| Forward current                              | IF     | 100         | mA   |
| Peak forward current                         | IFM    | 225         | mA   |
| Non-repetitive peak forward surge current *1 | IFSM   | 500         | mA   |
| Junction temperature                         | Tj     | 150         | °C   |
| Operating ambient temperature                | Topr   | -40 to +85  | °C   |
| Storage temperature                          | Tstg   | -55 to +150 | °C   |

Note)\*1: t = 1 s

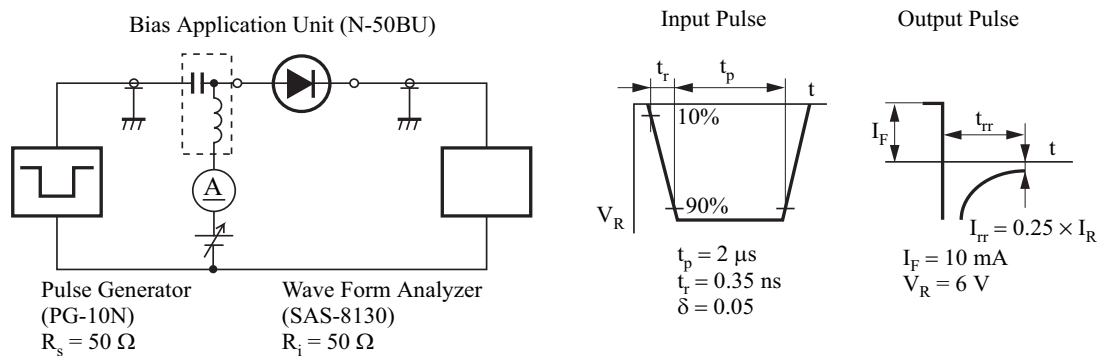




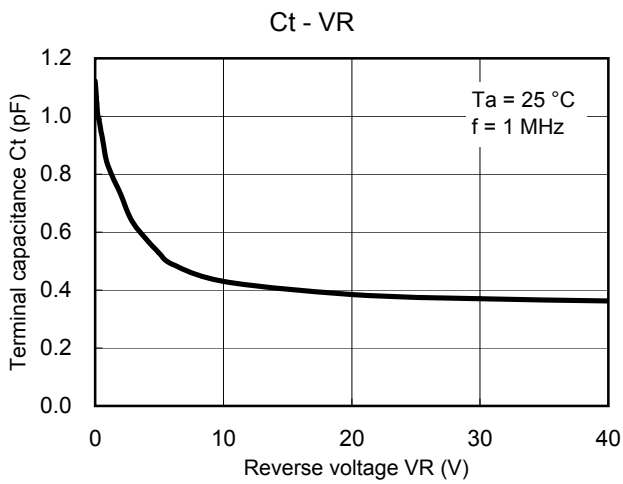
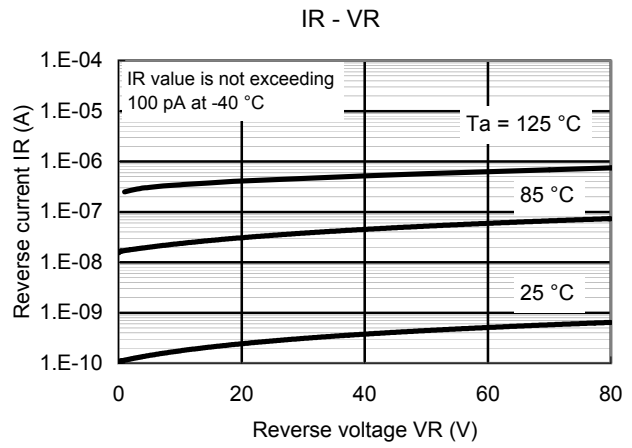
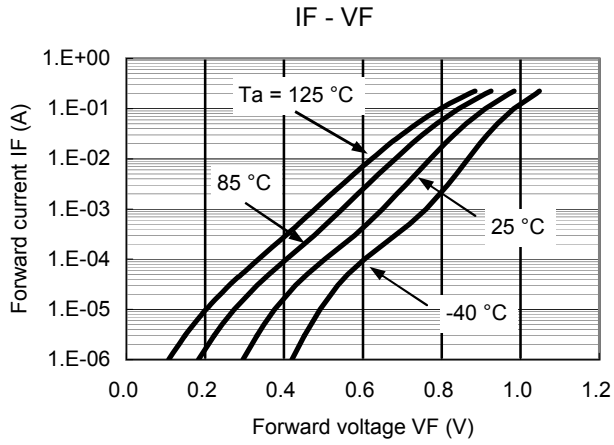
■ Electrical Characteristics  $T_a = 25\text{ }^\circ\text{C} \pm 3\text{ }^\circ\text{C}$

| Parameter                | Symbol          | Conditions  | Min | Typ  | Max  | Unit |
|--------------------------|-----------------|---|-----|------|------|------|
| Forward voltage          | VF              | IF = 100 mA   |     | 0.92 | 1.20 | V    |
| Reverse voltage          | VR              | IR = 100 $\mu$ A                                    | 80  |      |      | V    |
| Reverse current          | IR              | VR = 80 V   |     |      | 100  | nA   |
| Terminal capacitance     | Ct              | VR = 0 V, f = 1 MHz                                 |     |      | 2.0  | pF   |
| Reverse recovery time *1 | t <sub>rr</sub> | IF = 10 mA, VR = 6 V<br>I <sub>rr</sub> = 0.25 x IR |     |      | 3    | ns   |

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.  
 2. Absolute frequency of input and output is 100 MHz.  
 3. \*1: t<sub>rr</sub> test circuit



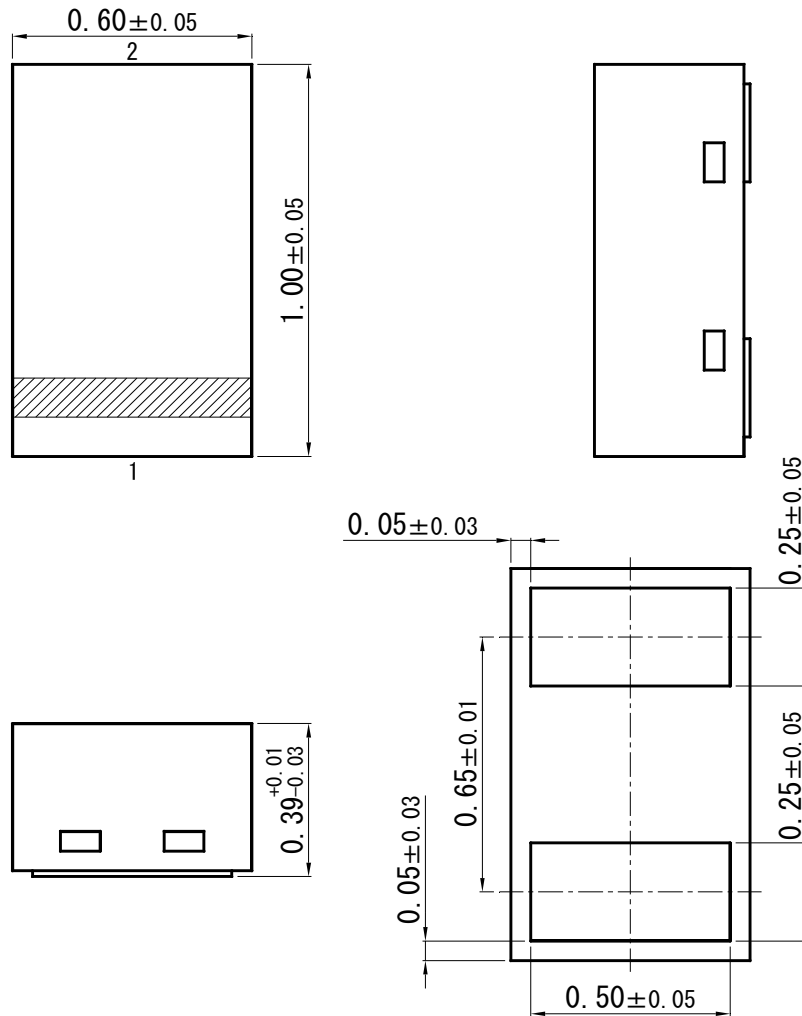
Technical Data ( reference )



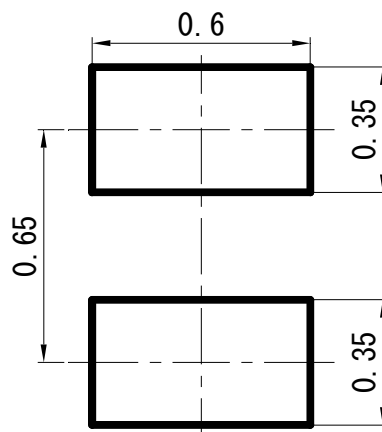


ML2-N3-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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